

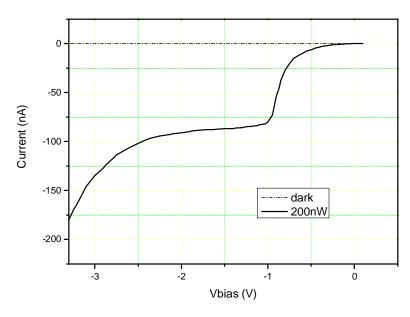
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Overview

- Building up equivalent circuit model of photoelectric device is quiet necessary before design the readout circuit.
- □ The equivalent circuit model is presented by combination with the result of curve fitting, and simulated with Cadence EDA platform.
- The circuit model could be optimized and could be linked with the readout circuit.
- The signification of the equivalent circuit model may be design an optimal readout circuit for the novel PD.

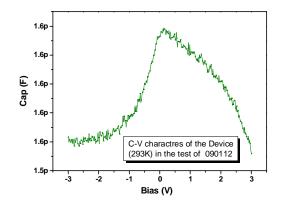
Characterizing of the photodetector



The electric current vs voltage (I-V) curve of near infrared low dimension photodetector was gained by the Keithly 4200-SCS at 1.3 μm photo source and room temperature.

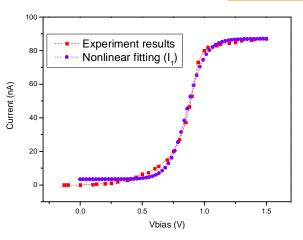
The range of bias voltage is from -4V to 0V and the voltage step 0.02V.

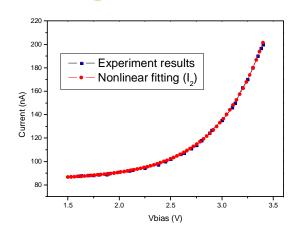
Characterizing of the photodetector



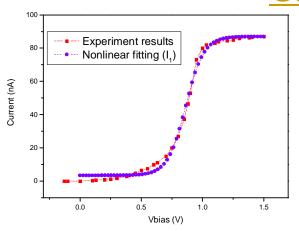
- The C-V curve was measured by a DC bias voltage and a smallsignal AC bias voltage added at same time.
- □ The range of the bias voltage was from -3V~+3V, the voltage step 0.02V and the 1MHz frequency at room temperature.

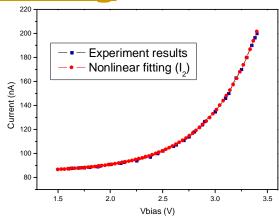
- Nonlinear fitting of I-V curve is completed by applying Origin software.
- Curve fitting includes full fitting and sectional fitting.
- The result of full fitting can be applied to circuit modeling directly. The sectional fitting is suitable for special curve and it is more accurate.





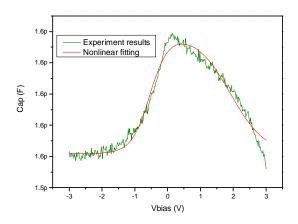
- The curves is divided into two sections at V_{bias}=1.5V, on the flat parts of the curve.
- Because the I-V curve shows exponential function relation, the fitting need change the direction of coordinate (abscissa and ordinate).





- Left Fig. shows the nonlinear fitting curve and experimental curve at V_{bias} range [0, 1.5].
- \blacksquare Right Fig. shows the curves at V_{bias} range [1.5, 3.5].
- □ The result of sectional fitting is given by:

$$\begin{cases} I_1 = 86.97 + \frac{3.35 - 86.97}{1 + e^{(V - 0.86)/0.07}} (nA) & V \in [0 \quad 1.5] \\ I_2 = 84.44 + 5.46 \times e^{(V - 1.94)/0.47} (nA)V \in [1.5 \quad 3.5] \end{cases}$$
 (2)



- The Fig. shows the nonlinear fitting curve and experimental curve for PD C-V.
- The intrinsic capacitance of the novel PD is composed of depletion capacitance and storage capacitance.
- In the optical radiation condition, the polarization effect of photogenerated carriers affects the intrinsic capacitance of the PD.
- The full fitting is suitable for C-V curve fitting.

Curve fitting

The result of full fitting is given by:

$$C_p = 1.56 + \frac{7.69}{1 + e^{-(V - 0.69 + 1.22)/0.28}}$$

$$\times (1 - \frac{1}{1 + e^{-(V - 0.69 - 1.22)/0.52}}) \qquad (pF)$$

Equivalent circuit modeling

- According to the result of I-V curve fitting above, the equivalent circuit model needs two voltage controlled current sources.
- A switching function is needed at the dividing point of the 1.5V, it can be achieved by the integral.
- The function can be expressed as follows:

$$K(V) = \text{int}(\frac{V - 1.5}{V - 1.5 - \delta})$$
 $0 < \delta << 1$

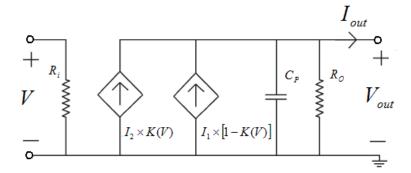
lue The K (V) is given by

$$K(V) = \begin{cases} 0 & V \in \begin{bmatrix} 0 & 1.5 \end{bmatrix} \\ 1 & V \in \begin{bmatrix} 1.5 & 3.5 \end{bmatrix} \end{cases}$$

Where V is the bias voltage of the PD and δ a constant.

Equivalent circuit modeling

According to the curve fitting of I-V and C-V, the equivalent circuit model is shown:



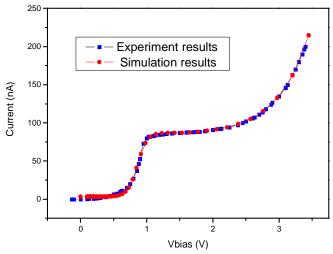
- Where C_p the intrinsic capacitance; R_0 , R_i the resistances;
- □ The current of PD severally at different range of bias voltage:

$$I_1 \times [1 - K(V)], I_2 \times K(V)$$

- \blacksquare The R_0 is an important parameter, it can be calculated from C-F curve.
- □ The parameters C_p , R_0 and K(V) are all the functions of bias voltage V.

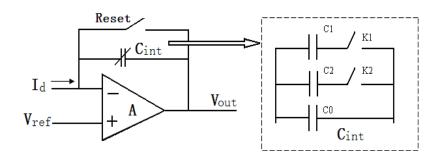
Simulation results

The signification of this equivalent circuit model is to design an optimal readout circuit for the PD.

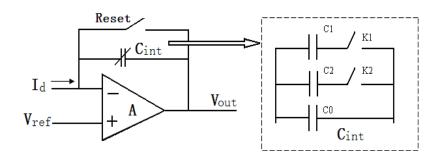


- The Fig. shows the simulation results of equivalent circuit model with Cadence EDA platform, which is consistent with the experiment date.
- It can be used as the signal source of readout circuit and matching with readout structure.

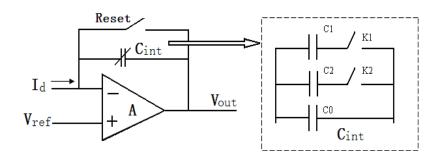
- The capacitor feedback transimpedance amplifier (CTIA) of the transition current to voltage used amplifying small signal is implemented by means of a low-noise preamplifier and a feedback capacitor.
- Based on the principle of charge conservation, the equation can be given by $C_{\text{int}} \times \Delta V = I_{d} \times T_{\text{int}}$
- lacktriangle Here, $T_{\rm int}$ is the feedback capacitor, $\varDelta V$ output voltage range, $I_{\rm d}$ PD current.
- T_{int} adjusts integration time for realizing CTIA performance.



- Because the novel PD has an I-V sudden change, a certain feedback capacitor is not suitable for large changes of current level.
- The method of turning C_{int} is proposed. The Fig. shows the design of optimal readout structure.
- \square Where, V_{ref} is reference voltage, Reset for reset switch of CTIA.



- The C_{int} is divided into three parts C_0 , C_1 and C_2 .
- The value of C_0 , C_1 , C_2 is each 1pF, 1pF, 2pF.
- Moreover, C_1 and C_2 are in series with switches K_1 and K_2 respectively. When the switch is 0, the switch off, otherwise is on state.

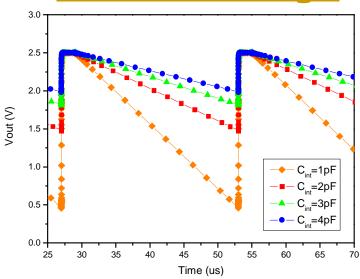


- \square When V_{bias} range in 0-1.5V, C_0 is suitable.
- □ When V_{bias} range in 1.5-3.5V, C_1 or C_2 should be in parallel with C_0 , and increase the value of the feedback capacitor.
- The states K₁ and K₂ could make different CTIA performances.

Readout Design

K2	K1	Cint (pF)	$T_{\text{int}} = 24 \text{us}, I_{\text{max}} \text{ (nA)}$	Output voltage range ΔV (V)
0	0	1	85	2
0	1	2	170	2
1	0	3	255	2
1	1	4	340	2

□ The Table shows: according to the I-V curve of the novel PD, K_1 and K_2 will be set in different state, while the bias voltage is set at different voltage range.



- □ The Fig. shows the simulation result of CTIA with different value of C_{int} .
- The CTIA can export optimal voltage level.

Summary

- An equivalent circuit model of a novel photoelectric detector has obtained by setting appropriate circuit parameters.
- The curve fitting was not only associating the bias voltage and the current (I-V), but also relating the bias voltage and the capacitance (C-V) of the PD.
- The accuracy of the model could be verified by simulating the circuit.
- The simulation results are in agreement with the experimental results.
- At last, a matched readout circuit structure based on the circuit model is designed and well readout the practicable response signal.

Thanks for your attention!